

Electronic Circuits

Handbook for Design
and Applications

U. Tietze
Ch. Schenk

2nd edition

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Ulrich Tietze • Christoph Schenk • Eberhard Gamm
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Preface

The purpose of this book is to help the reader to understand off-the-shelf circuits and to enable him to design his or her own circuitry. The book is written for students, practicing engineers and scientists. It covers all major aspects of analog and digital circuit design. The book is a translation of the current 12th edition of the German bestseller *Halbleiter-Schaltungstechnik*.

Part I describes semiconductor devices and their behavior with respect to the models used in circuit simulation. This part introduces all major aspects of transistor level design (IC-design). Basic circuits are analyzed in five steps: large-signal transfer characteristic, small-signal response, frequency response and bandwidth, noise and distortion. Digital circuits are covered starting with the internal circuitry of gates and flip-flops up to the construction of combinatorial and sequential logic systems with PLDs and FPGAs. Design examples and a short form guide for the digital synthesis tool *ispLever* are included on the CD enclosed.

Part II is dedicated to board level design. The main chapters of this part describe the use of operational amplifiers for signal conditioning including signal amplification, filtering and AD-conversion. Further chapters cover power amplifiers, power supplies and other important functional blocks of analog systems. The chapters are self-contained with a minimum of cross-reference. This allows the advanced reader to familiarize himself quickly with the various areas of applications. Each chapter offers a detailed overview of various solutions to a given requirement. In order to enable the reader to proceed quickly from an idea to a working circuit, we discuss only those solutions we have tested thoroughly by simulation. Many of these simulation examples are included on the CD enclosed.

Part III describes circuits for analog and digital communication over wireless channels. The first chapter is dedicated to transmission channels, scattering parameters and analog and digital modulations. Further chapters treat the architecture of transmitters and receivers, the high frequency behavior of components, circuits for impedance matching, high frequency amplifiers and mixers for frequency conversion.

To support analog circuit design, design examples and a short-form guide for the well known circuit simulator *PSpice* are included on the CD. This package contains libraries with examples of scalable transistors for IC-like design. The library also supports S-parameter and loop-gain simulations. An HTML-based index allows comfortable navigation throughout the simulations.

Our homepage www.tietze-schenk.com offers updates, supplements and design examples. We encourage you to use our email-address mail@tietze-schenk.com for feedback and comments.

We would like to thank Dr. Merkle at Springer Heidelberg for the administration, Gerhard Büsching for the translation and Danny Lewis at PTP-Berlin for the assembly of this book. In particular we like to thank Dr. Eberhard Gamm for the contribution of the first four chapters of circuit design fundamentals in part I and the chapters of communications in part III. We have added him as a young innovative author.

Overview

Part I. Device Models and Basic Circuits	1
1. Diodes	3
2. Bipolar Transistors	33
3. Field Effect Transistors	169
4. Amplifiers	269
5. Operational Amplifiers	483
6. Latching Circuits	587
7. Logic Families	611
8. Combinatorial Circuits	635
9. Sequential Logic Systems	659
10. Semiconductor Memories	689
Part II. General Applications	723
11. Operational Amplifier Applications	725
12. Controlled Sources and Impedance Converters	767
13. Active Filters	787
14. Signal Generators	843
15. Power Amplifiers	867
16. Power Supplies	885
17. Analog Switches and Sample-and-Hold Circuits	929
18. Digital-Analog and Analog-Digital Converters	945
19. Digital Filters	987
20. Measurement Circuits	1031
21. Sensors and Measurement Systems	1059
22. Electronic Controllers	1103
23. Optoelectronic Components	1127
Part III. Communication Circuits	1147
24. Basics	1149
25. Transmitters and Receivers	1237
26. Passive Components	1283
27. High-Frequency Amplifiers	1321
28. Mixers	1363
29. Appendix	1431
Bibliography	1525
Index	1529

Contents

Part I. Device Models and Basic Circuits	1
1. Diodes	3
1.1 Performance of the Diode	4
1.1.1 Characteristic Curve	4
1.1.2 Description by Equations	5
1.1.3 Switching Performance	8
1.1.4 Small-Signal Response	10
1.1.5 Limit Values and Reverse Currents	11
1.1.6 Thermal Performance	12
1.1.7 Temperature Sensitivity of Diode Parameters	12
1.2 Construction of a Diode	13
1.2.1 Discrete Diode	13
1.2.2 Integrated Diode	15
1.3 Model of a Diode	16
1.3.1 Static Performance	16
1.3.2 Dynamic Performance	19
1.3.3 Small-Signal Model	22
1.4 Special Diodes and Their Application	24
1.4.1 Zener Diode	24
1.4.2 Pin Diode	27
1.4.3 Varactor Diodes	28
1.4.4 Bridge Rectifier	30
1.4.5 Mixer	31
2. Bipolar Transistors	33
2.1 Performance of a Bipolar Transistor	34
2.1.1 Characteristics	34
2.1.2 Description by Way of Equations	36
2.1.3 Characteristic of the Current Gain	37
2.1.4 Operating Point and Small-Signal Response	39
2.1.5 Limit Data and Reverse Currents	45
2.1.6 Thermal Performance	49
2.1.7 Temperature Sensitivity of Transistor Parameters	53
2.2 Design of a Bipolar Transistor	54
2.2.1 Discrete Transistors	55
2.2.2 Integrated Transistors	56

2.3	Models of Bipolar Transistors	58
2.3.1	Static Performance	58
2.3.2	Dynamic Performance	68
2.3.3	Small-Signal Model	73
2.3.4	Noise	82
2.4	Basic Circuits	95
2.4.1	Common-Emitter Circuit	96
2.4.2	Common-Collector Circuit	131
2.4.3	Common-Base Circuit	148
2.4.4	Darlington Circuit	159
3.	Field Effect Transistors	169
3.1	Behavior of a Field Effect Transistor	170
3.1.1	Characteristic Curves	172
3.1.2	Description by Equations	175
3.1.3	Field Effect Transistor as an Adjustable Resistor	179
3.1.4	Operating Point and Small-Signal Behavior	181
3.1.5	Maximum Ratings and Leakage Currents	185
3.1.6	Thermal Behavior	189
3.1.7	Temperature Sensitivity of FET Parameters	189
3.2	Construction of the Field Effect Transistor	192
3.2.1	Integrated MOSFETs	192
3.2.2	Discrete MOSFETs	194
3.2.3	Junction FETs	197
3.2.4	Cases	197
3.3	Models of Field Effect Transistors	197
3.3.1	Static Behavior	198
3.3.2	Dynamic Behavior	206
3.3.3	Small-Signal Model	215
3.3.4	Noise	222
3.4	Basic Circuits	229
3.4.1	Common-Source Circuit	230
3.4.2	Common-Drain Circuit	252
3.4.3	Common-Gate Circuit	261
4.	Amplifiers	269
4.1	Circuits	271
4.1.1	Current Sources and Current Mirrors	277
4.1.2	Cascode circuit	312
4.1.3	Differential Amplifier	327
4.1.4	Impedance Converters	385
4.1.5	Circuits for Setting the Operating Point	395
4.2	Properties and Parameters	408

4.2.1	Characteristics	409
4.2.2	Small-Signal Characteristics	412
4.2.3	Nonlinear Parameters	426
4.2.4	Noise	443
5.	Operational Amplifiers	483
5.1	General	483
5.1.1	Types of Operational Amplifier	484
5.1.2	Principle of Negative Feedback	487
5.2	Normal Operational Amplifier (VV-OPA)	491
5.2.1	Principle	492
5.2.2	Multipurpose Amplifiers	494
5.2.3	Operating Voltages	497
5.2.4	Single-Supply Amplifiers	498
5.2.5	Rail-to-Rail Amplifiers	500
5.2.6	Wide-Band Operational Amplifiers	504
5.2.7	Frequency Compensation	509
5.2.8	Parameters of Operational Amplifiers	523
5.3	Transconductance Amplifier (VC-OPA)	540
5.3.1	Internal Construction	541
5.3.2	Typical Applications	543
5.4	Transimpedance Amplifier (CV-OPA)	544
5.4.1	Internal Design	545
5.4.2	Frequency Response	550
5.4.3	Typical Applications	551
5.5	The Current Amplifier (CC-OPA)	552
5.5.1	The Internal Design	552
5.5.2	Typical Applications	554
5.6	Comparison	568
5.6.1	Practical Implementation	570
5.6.2	Types	572
6.	Latching Circuits	587
6.1	Transistor as Switch	587
6.2	Latching Circuits Using Saturated Transistors	590
6.2.1	Bistable Circuits	591
6.2.2	Monostable Circuits	593
6.2.3	Astable Circuits (Multivibrators)	594
6.3	Latching Circuits with Emitter-Coupled Transistors	595
6.3.1	Emitter-Coupled Schmitt Trigger	595
6.3.2	Emitter-Coupled Multivibrator	595
6.4	Latching Circuits Using Gates	597
6.4.1	Flip-Flops	597

6.4.2	One-Shot	597
6.4.3	Multivibrator	598
6.5	Latching Circuits Using Comparators	600
6.5.1	Comparators	600
6.5.2	Schmitt Trigger	601
6.5.3	Multivibrators	604
6.5.4	One-Shots	607
7.	Logic Families	611
7.1	Basic Logic Functions	611
7.2	Construction of Logic Functions	614
7.2.1	Karnaugh Map	615
7.3	Extended Functions	617
7.4	Circuit Implementation of the Basic Functions	618
7.4.1	Resistor-Transistor Logic (RTL)	619
7.4.2	Diode-Transistor Logic (DTL)	620
7.4.3	High-Level Logic (HLL)	620
7.4.4	Transistor-Transistor Logic (TTL)	621
7.4.5	Emitter-Coupled Logic (ECL)	624
7.4.6	Complementary MOS Logic (CMOS)	627
7.4.7	NMOS Logic	631
7.4.8	Summary	631
7.5	Connecting Lines	633
8.	Combinatorial Circuits	635
8.1	Number Representation	636
8.1.1	Positive Integers in Straight Binary Code	636
8.1.2	Positive Integers in BCD Code	637
8.1.3	Binary Integers of Either Sign	637
8.1.4	Fixed-Point Binary Numbers	640
8.1.5	Floating-Point Binary Numbers	640
8.2	Multiplexer – Demultiplexer	643
8.2.1	1-of-n Decoder	643
8.2.2	Demultiplexer	644
8.2.3	Multiplexer	645
8.3	Priority Decoder	646
8.4	Combinatorial Shift Register (Barrel Shifter)	647
8.5	Digital Comparators	648
8.6	Adders	650
8.6.1	Half-Adder	650
8.6.2	Full-Adder	651
8.6.3	Look-Ahead Carry Logic	652
8.6.4	Subtraction	654

8.6.5	Two's-Complement Overflow	654
8.6.6	Addition and Subtraction of Floating-Point Numbers	655
8.7	Multipliers	656
8.7.1	Multiplication of Fixed-Point Numbers	656
8.7.2	Multiplication of Floating-Point Numbers	658
9.	Sequential Logic Systems	659
9.1	Integrated Flip-Flops	659
9.1.1	Transparent Flip-Flops	659
9.1.2	Flip-Flops with Intermediate Storage	661
9.2	Straight Binary Counters	666
9.2.1	Asynchronous Straight Binary Counters	667
9.2.2	Synchronous Straight Binary Counters	667
9.2.3	Up–Down Counters	669
9.3	BCD Counters	673
9.3.1	Asynchronous BCD Counters	673
9.3.2	Synchronous BCD Counters	674
9.4	Presetable Counters	675
9.5	Shift Registers	676
9.5.1	Basic Circuit	676
9.5.2	Shift Registers with Parallel Inputs	677
9.6	Processing of Asynchronous Signals	677
9.6.1	Debouncing of Mechanical Contacts	678
9.6.2	Edge-Triggered RS Flip-Flops	678
9.6.3	Pulse Synchronization	679
9.6.4	Synchronous One-Shot	680
9.6.5	Synchronous Edge Detector	681
9.6.6	Synchronous Clock Switch	681
9.7	Systematic Design of Sequential Circuits	682
9.7.1	State Diagram	682
9.7.2	Example for a Programmable Counter	684
9.8	Dependency notation	686
10.	Semiconductor Memories	689
10.1	Random Access Memories (RAMs)	690
10.1.1	Static RAMs	690
10.1.2	Dynamic RAMs	693
10.2	RAM Expansions	697
10.2.1	Two-Port Memories	697
10.2.2	RAMs as Shift Registers	698
10.2.3	First-In-First-Out Memories (FIFO)	700
10.2.4	Error Detection and Correction	702
10.3	Read-Only Memories (ROMs)	706

10.3.1	Mask-Programmed ROMs (MROMs)	706
10.3.2	Programmable ROMs (PROMs)	706
10.3.3	UV-Erasable PROMs (EPROMs)	707
10.3.4	Electrically Erasable PROMs (EEPROMs)	709
10.4	Programmable Logic Devices (PLDs)	711
10.4.1	Programmable Logic Array (PAL)	714
10.4.2	Computer-Aided PLD Design	715
10.4.3	Survey of Types Available	717
10.4.4	User Programable Gate Arrays	719

Part II. General Applications 723

11. Operational Amplifier Applications 725

11.1	Summing Amplifier	725
11.2	Subtracting Circuits	726
11.2.1	Reduction to an Addition	726
11.2.2	Subtraction Using a Single Operational Amplifier	727
11.3	Bipolar-Coefficient Circuit	729
11.4	Integrators	730
11.4.1	Inverting Integrator	730
11.4.2	Initial Condition	733
11.4.3	Summing Integrator	734
11.4.4	Noninverting Integrator	734
11.5	Differentiators	735
11.5.1	Basic Circuit	735
11.5.2	Practical Implementation	736
11.5.3	Differentiator with High Input Impedance	737
11.6	Solving Differential Equations	738
11.7	Function Networks	739
11.7.1	Logarithm	740
11.7.2	Exponential Function	743
11.7.3	Computation of Power Functions Using Logarithms	744
11.7.4	Sine and Cosine Functions	745
11.7.5	Arbitrary Function Networks	750
11.8	Analog Multipliers	753
11.8.1	Multipliers with Logarithmic Amplifiers	753
11.8.2	Transconductance Multipliers	754
11.8.3	Multipliers Using Electrically Controlled Resistors	759
11.8.4	Adjustment of Multipliers	761
11.8.5	Expansion to Four-Quadrant Multipliers	761
11.8.6	Multiplier as a Divider or Square Rooter	762
11.9	Transformation of Coordinates	763

11.9.1	Transformation from Polar to Cartesian Coordinates	763
11.9.2	Transformation from Cartesian to Polar Coordinates	764
12.	Controlled Sources and Impedance Converters	767
12.1	Voltage-Controlled Voltage Sources	767
12.2	Current-Controlled Voltage Sources	768
12.3	Voltage-Controlled Current Sources	769
12.3.1	Current Sources for Floating Loads	769
12.3.2	Current Sources for Grounded Loads	771
12.3.3	Precision Current Sources Using Transistors	772
12.3.4	Floating Current Sources	777
12.4	Current-Controlled Current Sources	778
12.5	NIC (Negative Impedance Converter)	779
12.6	Gyrator	781
12.7	Circulator	784
13.	Active Filters	787
13.1	Basic Theory of Lowpass Filters	787
13.1.1	Butterworth Lowpass Filters	791
13.1.2	Chebyshev Lowpass Filters	793
13.1.3	Bessel Lowpass Filters	796
13.1.4	Summary of the Theory	805
13.2	Lowpass/Highpass Transformation	806
13.3	Realization of First-Order Lowpass and Highpass Filters	807
13.4	Realization of Second-Order Lowpass and Highpass Filters	809
13.4.1	<i>LRC</i> Filters	809
13.4.2	Filters with Multiple Negative Feedback	809
13.4.3	Filter with Single Positive Feedback	810
13.5	Realization of Higher-Order Lowpass and Highpass Filters	813
13.6	Lowpass/Bandpass Transformation	815
13.6.1	Second-Order Bandpass Filters	816
13.6.2	Fourth-Order Bandpass Filters	816
13.7	Realization of Second-Order Bandpass Filters	819
13.7.1	<i>LRC</i> Bandpass Filter	820
13.7.2	Bandpass Filter with Multiple Negative Feedback	820
13.7.3	Bandpass Filter with Single Positive Feedback	822
13.8	Lowpass/Bandstop Filter Transformation	823
13.9	Realization of Second-Order Bandstop Filters	824
13.9.1	<i>LRC</i> Bandstop Filter	824
13.9.2	Active Parallel- <i>T</i> Bandstop Filter	825
13.9.3	Active Wien–Robinson Bandstop Filter	825
13.10	Allpass Filters	826
13.10.1	Basic Principles	826

13.10.2 Realization of First-Order Allpass Filters	829
13.10.3 Realization of Second-Order Allpass Filters	829
13.11 Adjustable Universal Filters	831
13.12 Switched Capacitor Filters	836
13.12.1 Principle	836
13.12.2 SC Integrator	836
13.12.3 First-Order SC Filter	837
13.12.4 Second-Order SC Filters	838
13.12.5 Implementation of SC Filters with ICs	840
13.12.6 General Considerations for Using SC Filters	840
13.12.7 A Survey of Available Types	840
14. Signal Generators	843
14.1 LC Oscillators	843
14.1.1 Condition for Oscillation	843
14.1.2 Meissner Oscillator	845
14.1.3 Hartley Oscillator	846
14.1.4 Colpitts Oscillator	847
14.1.5 Emitter-Coupled LC Oscillator	847
14.1.6 Push–Pull Oscillators	848
14.2 Crystal Oscillators	849
14.2.1 Electrical Characteristics of a Quartz Crystal	849
14.2.2 Fundamental Frequency Oscillators	850
14.2.3 Harmonic Oscillators	852
14.3 Wien–Robinson Oscillator	853
14.4 Differential-Equation Oscillators	857
14.5 Function Generators	859
14.5.1 Basic Arrangement	860
14.5.2 Practical Implementation	861
14.5.3 Function Generators with a Controllable Frequency	862
14.5.4 Simultaneously Producing Sine and Cosine Signals	864
15. Power Amplifiers	867
15.1 Emitter Follower as a Power Amplifier	867
15.2 Complementary Emitter Followers	869
15.2.1 Complementary Class-B Emitter Follower	869
15.2.2 Complementary Class-AB Emitter Followers	871
15.2.3 Generation of the Bias Voltage	872
15.3 Complementary Darlington Circuits	874
15.4 Complementary Source Followers	875
15.5 Current Limitation	876
15.6 Four-Quadrant Operation	878
15.7 Design of a Power Output Stage	879

15.8	Driver Circuits with Voltage Gain	882
15.9	Boosting the Output Current of Integrated Operational Amplifiers	884
16.	Power Supplies	885
16.1	Properties of Power Transformers	885
16.2	Power Rectifiers	886
16.2.1	Half-Wave Rectifier	886
16.2.2	Bridge Rectifier	887
16.2.3	Center-Tap Rectifier	891
16.3	Linear Voltage Regulators	892
16.3.1	Basic Regulator	892
16.3.2	Voltage Regulators with a Fixed Output Voltage	893
16.3.3	Voltage Regulators with an Adjustable Output Voltage	895
16.3.4	A Voltage Regulator with a Reduced Dropout Voltage	896
16.3.5	A Voltage Regulator for Negative Voltages	897
16.3.6	Symmetrical Division of a Floating Voltage	898
16.3.7	Voltage Regulator with Sensor Terminals	899
16.3.8	Bench Power Supplies	900
16.3.9	IC Voltage Regulators	901
16.4	Reference Voltage Generation	901
16.4.1	Zener Diode References	901
16.4.2	Bandgap Reference	904
16.4.3	Types	906
16.5	Switched-Mode Power Supplies	907
16.6	Secondary Switching Regulators	908
16.6.1	Step-Down Converters	908
16.6.2	Generating the Switching Signal	911
16.6.3	Step-Up Converters	913
16.6.4	Inverting Converter	914
16.6.5	Charge Pump Converter	914
16.6.6	Integrated Switching Regulators	915
16.7	Primary Switching Regulators	916
16.7.1	Single-Ended Converters	917
16.7.2	Push-Pull Converters	918
16.7.3	High-Frequency Transformers	920
16.7.4	Power Switches	921
16.7.5	Generating the Switching Signals	924
16.7.6	Loss Analysis	925
16.7.7	IC Drive Circuits	926
17.	Analog Switches and Sample-and-Hold Circuits	929
17.1	Principle	929

17.2	Electronic Switches	930
17.2.1	FET Switch	930
17.2.2	Diode Switch	933
17.2.3	Bipolar Transistor Switch	935
17.2.4	Differential Amplifier Switch	937
17.3	Analog Switches Using Amplifiers	939
17.3.1	Analog Switches for High Voltages	940
17.3.2	Amplifier with Switchable Gain	940
17.4	Sample-and-Hold Circuits	941
17.4.1	Basic Principles	941
17.4.2	Practical Implementation	943
18.	Digital-Analog and Analog-Digital Converters	945
18.1	Sampling Theorem	945
18.1.1	Practical Aspects	947
18.2	Resolution	950
18.3	Principles of D/A Conversion	951
18.4	D/A Converters in CMOS Technology	952
18.4.1	Summation of Weighted Currents	952
18.4.2	D/A Converters with Double-Throw Switches	952
18.4.3	Ladder Network	953
18.4.4	Inverse Operation of a Ladder Network	954
18.5	A Ladder Network for Decade Weighting	955
18.6	D/A Converters in Bipolar Technology	956
18.7	D/A Converters for Special Applications	958
18.7.1	Processing Signed Numbers	958
18.7.2	Multiplying D/A Converters	960
18.7.3	Dividing D/A Converters	960
18.7.4	D/A Converter as Function Generator	961
18.8	Accuracy of DA Converters	963
18.8.1	Static Errors	963
18.8.2	Dynamic Characteristics	964
18.9	Principles of A/D Conversion	966
18.10	Design of A/D Converters	967
18.10.1	Parallel Converter	967
18.10.2	Two Step Converters	969
18.10.3	Successive Approximation	972
18.10.4	Counting Method	975
18.10.5	Oversampling	979
18.11	Errors in AD-Converters	983
18.11.1	Static Errors	983
18.11.2	Dynamic Errors	984
18.12	Comparison of AD-Converters	985

19. Digital Filters	987
19.1 Digital Transfer Function	988
19.1.1 Time Domain Analysis	988
19.1.2 Frequency Domain Analysis	988
19.2 Basic Structures	991
19.3 Design Analysis of FIR Filters	994
19.3.1 Basic Equations	995
19.3.2 Simple Examples	996
19.3.3 Calculating the Filter Coefficients	1000
19.4 Realization of FIR Filters	1013
19.4.1 Realization of FIR Filters Using the Parallel Method	1014
19.4.2 Realization of FIR Filters Using the Serial Method	1014
19.5 Design of IIR Filters	1015
19.5.1 Calculating the Filter Coefficients	1016
19.5.2 IIR Filters in a Cascade Structure	1018
19.6 Realization of IIR Filters	1022
19.6.1 Construction from Simple Building Blocks	1022
19.6.2 Design Using LSI Devices	1025
19.7 Comparison of FIR and IIR Filters	1027
20. Measurement Circuits	1031
20.1 Measurement of Voltage	1031
20.1.1 Impedance Converter	1031
20.1.2 Measurement of Potential Difference	1032
20.1.3 Isolation Amplifiers	1037
20.2 Measurement of Current	1040
20.2.1 Floating Zero-Resistance Ammeter	1040
20.2.2 Measurement of Current at High Potentials	1041
20.3 AC/DC Converters	1042
20.3.1 Measurement of the Mean Absolute Value	1042
20.3.2 Measurement of the rms Value	1046
20.3.3 Measurement of the Peak Value	1050
20.3.4 Synchronous Demodulator	1053
21. Sensors and Measurement Systems	1059
21.1 Temperature Measurement	1059
21.1.1 Metals as PTC Thermistors	1062
21.1.2 Silicon-Based PTC Thermistors	1062
21.1.3 NTC Thermistors	1063
21.1.4 Operation of Resistive Temperature Detectors	1063
21.1.5 Transistors as Temperature Sensors	1068
21.1.6 Thermocouple	1071
21.1.7 An Overview of Types	1075

21.2	Pressure Measurement	1076
21.2.1	Design of Pressure Sensors	1077
21.2.2	The Operation of Temperature-Compensated Pressure Sensors	1079
21.2.3	Temperature Compensation for Pressure Sensors	1082
21.2.4	Commercially Available Pressure Sensors	1085
21.3	Humidity Measurement	1086
21.3.1	Humidity Sensors	1087
21.3.2	Interfacing Circuits for Capacitive Humidity Sensors	1088
21.4	The Transmission of Sensor Signals	1090
21.4.1	Electrical (Direct-Coupled) Signal Transmission	1090
21.4.2	Electrically Isolated Signal Transmission	1093
21.5	Calibration of Sensor Signals	1094
21.5.1	Calibration of the Analog Signal	1095
21.5.2	Computer-Aided Calibration	1098
22.	Electronic Controllers	1103
22.1	Underlying Principles	1103
22.2	Controller Types	1104
22.2.1	P-controller	1104
22.2.2	PI-Controller	1106
22.2.3	PID-Controller	1108
22.2.4	The PID-Controller with Adjustable Parameters	1110
22.3	Control of Nonlinear Systems	1112
22.3.1	Static Nonlinearity	1112
22.3.2	Dynamic Nonlinearity	1113
22.4	Phase-Locked Loop	1114
22.4.1	Sample-and-Hold Circuit as a Phase Detector	1116
22.4.2	Synchronous Demodulator as a Phase Detector	1118
22.4.3	The Frequency-Sensitive Phase Detector	1120
22.4.4	The Phase Detector with an Extensible Measuring Range	1122
22.4.5	The PLL as a Frequency Multiplier	1123
23.	Optoelectronic Components	1127
23.1	Basic Photometric Terms	1127
23.2	Photoconductive Cells	1129
23.3	Photodiodes	1130
23.4	Phototransistors	1132
23.5	Light-Emitting Diodes	1133
23.6	Optocouplers	1134
23.7	Visual Displays	1134
23.7.1	Binary Displays	1135
23.7.2	Analog Displays	1136
23.7.3	Numerical Displays	1138

23.7.4	Multiplex Displays	1139
23.7.5	Alphanumeric Displays	1141

Part III. Communication Circuits **1147**

24. Basics **1149**

24.1	Telecommunication Systems	1149
24.2	Transmission Channels	1152
24.2.1	Cable	1152
24.2.2	Radio Communication	1163
24.2.3	Fibre Optic Links	1168
24.2.4	Comparison of Transmission Channels	1173
24.3	Reflection Coefficient and S Parameters	1174
24.3.1	Wave Parameters	1174
24.3.2	Reflection Coefficient	1175
24.3.3	Wave Source	1181
24.3.4	S Parameters	1183
24.4	Modulation Methods	1191
24.4.1	Amplitude Modulation	1194
24.4.2	Frequency Modulation	1202
24.4.3	Digital Modulation Methods	1209
24.5	Multiple Use and Grouping of Communication Channels	1227
24.5.1	Multiplex Operation	1227
24.5.2	Duplex Operation	1234

25. Transmitters and Receivers **1237**

25.1	Transmitters	1237
25.1.1	Transmitters with Analogue Modulation	1237
25.1.2	Transmitters with Digital Modulation	1243
25.1.3	Generating Local Oscillator Frequencies	1244
25.2	Receivers	1245
25.2.1	Direct-Detection Receivers	1246
25.2.2	Superheterodyne Receivers	1247
25.2.3	Gain Control	1253
25.2.4	Dynamic Range of a Receiver	1259
25.2.5	Receivers for Digital Modulation	1265

26. Passive Components **1283**

26.1	High-Frequency Equivalent Circuits	1283
26.1.1	Resistor	1284
26.1.2	Inductor	1286
26.1.3	Capacitor	1288
26.2	Filters	1289

26.2.1	LC-Filters	1290
26.2.2	Dielectric Filters	1296
26.2.3	SAW Filters	1298
26.3	Circuits for Impedance Transformation	1301
26.3.1	Impedance Matching	1301
26.3.2	Coupling	1311
26.4	Power Splitters and Hybrids	1314
26.4.1	Power Splitter	1315
26.4.2	Hybrids	1316
27.	High-Frequency Amplifiers	1321
27.1	Integrated High-Frequency Amplifiers	1321
27.1.1	Impedance Matching	1322
27.1.2	Noise Figure	1324
27.2	High-Frequency Amplifiers with Discrete Transistors	1327
27.2.1	Generalized Discrete Transistor	1327
27.2.2	Setting the Operating Point (Biasing)	1329
27.2.3	Impedance Matching for a Single-Stage Amplifier	1332
27.2.4	Impedance Matching in Multi-stage Amplifiers	1338
27.2.5	Neutralization	1340
27.2.6	Special Circuits for Improved Impedance Matching	1343
27.2.7	Noise	1346
27.3	Broadband Amplifiers	1349
27.3.1	Principle of a Broadband Amplifier	1349
27.3.2	Design of a Broadband Amplifier	1351
27.4	Power Gain	1354
27.4.1	Direct Power Gain	1355
27.4.2	Insertion Gain	1356
27.4.3	Transfer Gain	1357
27.4.4	Available Power Gain	1358
27.4.5	Comparison of Gain Definitions	1358
27.4.6	Gain with Impedance Matching at Both Sides	1359
27.4.7	Maximum Power Gain with Transistors	1360
28.	Mixers	1363
28.1	Functional Principle of an Ideal Mixer	1363
28.1.1	Up-Conversion Mixer	1364
28.1.2	Down-Conversion Mixer	1365
28.2	Functional Principles of Practical Mixers	1367
28.2.1	Additive Mixing	1367
28.2.2	Multiplicative Mixers	1376
28.3	Mixers with Diodes	1381
28.3.1	Unbalanced Diode Mixer	1381

28.3.2	Single Balanced Diode Mixers	1391
28.3.3	Double Balanced Diode Mixer	1395
28.3.4	Diode Mixers in Practical Use	1401
28.4	Mixers with Transistors	1404
28.4.1	Single Balanced Mixer	1404
28.4.2	Double Balanced Mixer (Gilbert Mixer)	1417
29.	Appendix	1431
29.1	PSpice – Brief User’s Guide	1431
29.1.1	General	1431
29.1.2	Programs and Files	1431
29.1.3	A Simple Example	1434
29.1.4	Further Examples	1450
29.1.5	Integrating Other Libraries	1455
29.1.6	Some Typical Errors	1457
29.2	ispLEVER – Brief User’s Guide	1459
29.2.1	Outline	1459
29.2.2	Circuit Entry	1461
29.2.3	Pin Assignment	1475
29.2.4	Simulation	1479
29.2.5	Optimization	1484
29.2.6	Programming	1484
29.2.7	Outlook	1487
29.3	Passiv RC and LRC Networks	1488
29.3.1	The Lowpass Filter	1488
29.3.2	The Highpass Filter	1491
29.3.3	Compensated Voltage Divider	1494
29.3.4	Passive RC Bandpass Filter	1495
29.3.5	Wien–Robinson Bridge	1495
29.3.6	Parallel-T Filter	1497
29.3.7	Resonant Circuit	1498
29.4	Definitions and Nomenclature	1500
29.5	Types of the 7400 Digital Families	1508
29.6	Standard Series	1515
29.7	Color code	1516
29.8	Manufacturers	1518
	Bibliography	1525
	Index	1529

Part I

Device Models and Basic Circuits

Chapter 1:

Diode

The diode is a semiconductor component with two connections, which are called the *anode* (A) and the *cathode* (K). Distinction has to be made between discrete diodes, which are intended for installation on printed circuit boards and are contained in an individual case, and integrated diodes, which are produced together with other semiconductor components on a common semiconductor carrier (*substrate*). Integrated diodes have a third connection resulting from the common carrier. It is called the *substrate* (S); it is of minor importance for electrical functions.

Construction: Diodes consist of a pn or a metal-n junction and are called pn or Schottky diodes, respectively. Figure 1.1 shows the graphic symbol and the construction of a diode. In pn diodes the p and the n regions usually consist of silicon. Some discrete diode types still use germanium and thus have a lower forward voltage, but they are considered obsolete. In Schottky diodes the p region is replaced by a metal region. This type also has a low forward voltage and is therefore used to replace germanium pn diodes.

In practice the term *diode* is used for the silicon pn diode; all other types are identified by supplements. Since the same graphic symbol is used for all types of diodes with the exception of some special diodes the various types of discrete diodes can be distinguished only by means of the type number printed on the component or the specifications in the data sheet.

Operating modes: A diode can be operated in the *forward*, *reverse* or *breakthrough* mode. In the following Section these operating regions are described in more detail.

Diodes that are used predominantly for the purpose of rectifying alternating voltages are called *rectifier diodes*; they operate alternately in the forward and reverse region. Diodes designed for the operation in the breakthrough region are called *Zener diodes* and are used for voltage stabilization. The *variable capacitance diodes* are another important type. They are operated in the reverse region and, due to the particularly strong response of the junction capacitance to voltage variations, are used for tuning the frequency in resonant circuits. In addition, there is a multitude of special diodes which are not covered here in detail.

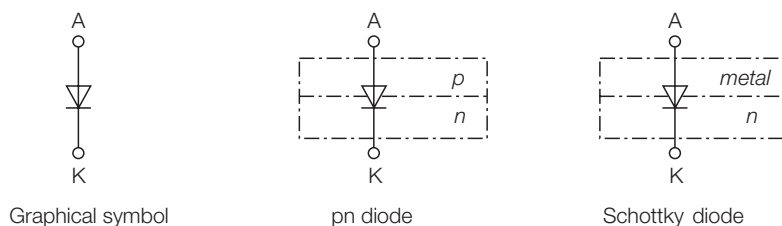


Fig. 1.1. Graphical symbol and diode construction

1.1 Performance of the Diode

The performance of a diode is described most clearly by its characteristic curve. This shows the relation between current and voltage where all parameters are *static* which means that they do not change over time or only very slowly. In addition, formulas that describe the diode performance sufficiently accurately are required for mathematical calculations. In most cases simple equations can be used. In addition, there is a model that correctly reflects the *dynamic performance* when the diode is driven with sinusoidal or pulse-shaped signals. This model is described in Sect. 1.3 and knowledge of it is not essential to understand the fundamentals. The following Sections focus primarily on the performance of silicon pn diodes.

1.1.1 Characteristic Curve

Connecting a silicon pn diode to a voltage $V_D = V_{AK}$ and measuring the current I_D in a positive sense from A to K results in the characteristic curve shown in Fig. 1.2. It should be noted that the positive voltage range has been enhanced considerably for reasons of clarity. For $V_D > 0\text{ V}$ the diode operates in the forward mode, i.e. in the *conducting state*. In this region the current rises exponentially with an increasing voltage. When $V_D > 0.4\text{ V}$, a considerable current flows. If $-V_{BR} < V_D < 0\text{ V}$ the diode is in the reverse-biased state and only a negligible current flows. This region is called the *reverse region*. The *breakthrough voltage* V_{BR} depends on the diode and for rectifier diodes amounts to $V_{BR} = 50 \dots 1000\text{ V}$. If $V_D < -V_{BR}$, the diode breaks through and a current flows again. Only Zener diodes are operated permanently in this *breakthrough region*; with all other diodes current flow with negative voltages is not desirable. With germanium and Schottky diodes a considerable current flows in the forward region even for $V_D > 0.2\text{ V}$, and the breakthrough voltage V_{BR} is $10 \dots 200\text{ V}$.

In the forward region the voltage for typical currents remains almost constant due to the pronounced rise of the characteristic curve. This voltage is called the *forward voltage* V_F .

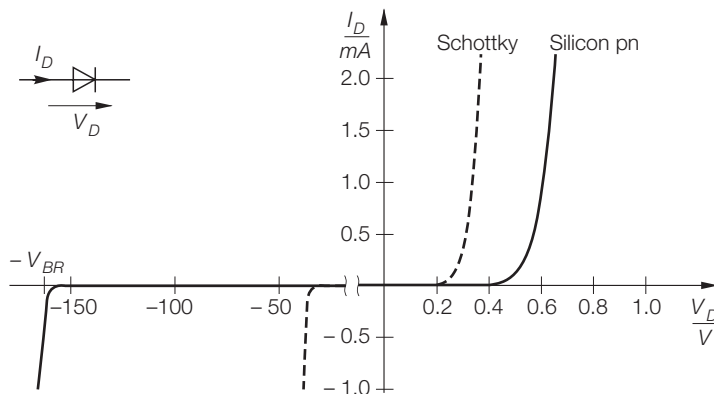


Fig. 1.2. Current-voltage characteristic of a small-signal diode

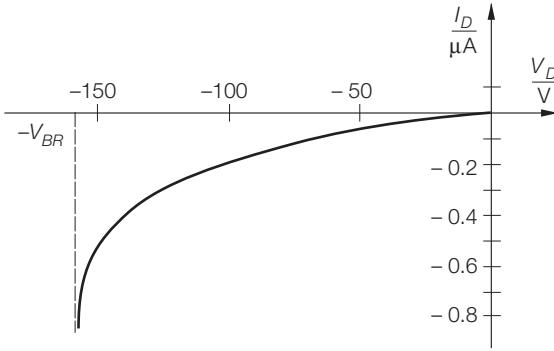


Fig. 1.3. Characteristic curve of a small-signal diode in the reverse region

and for both germanium and Schottky diodes lies at $V_{F,Ge} \approx V_{F,Schottky} \approx 0.3 \dots 0.4 \text{ V}$ and for silicon pn diodes at $V_{F,Si} \approx 0.6 \dots 0.7 \text{ V}$. With currents in the ampere range as used in power diodes the voltage may be significantly higher since in addition to the *internal* forward voltage a considerable voltage drop occurs across the spreading and connection resistances of the diode: $V_F = V_{F,i} + I_D R_B$. In the borderline case of $I_D \rightarrow \infty$ the diode acts like a very low resistance with $R_B \approx 0.01 \dots 10 \Omega$.

Figure 1.3 shows the enlarged reverse region. The *reverse current* $I_R = -I_D$ is very small with a low reverse voltage $V_R = -V_D$ and increases slowly when the voltage approaches the breakthrough voltage while it shoots up suddenly at the onset of the breakthrough.

1.1.2 Description by Equations

Plotting the characteristic curve for the region $V_D > 0$ in a semilogarithmic form results approximately in a straight line (see Fig. 1.4); this means that there is an exponential relation between I_D and V_D due to $\ln I_D \sim V_D$. The calculation on the basis of semiconductor physics leads to [1.1]:

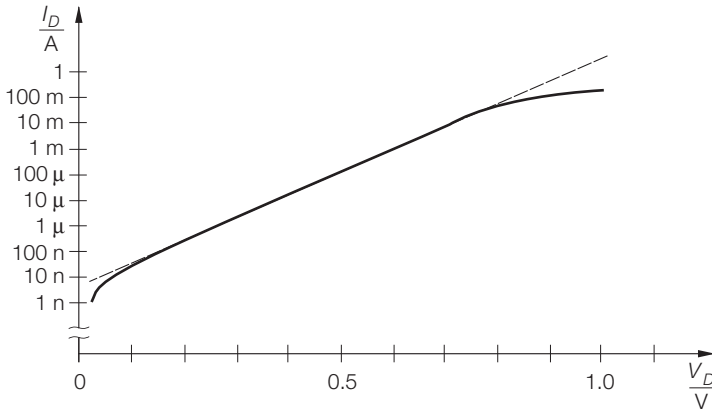


Fig. 1.4. Semilogarithmic representation of the characteristic curve for $V_D > 0$

$$I_D(V_D) = I_S \left(e^{\frac{V_D}{V_T}} - 1 \right) \quad \text{for } V_D \geq 0$$

For the correct description of a real diode a correction factor is required which enables the slope of the straight line in the semilogarithmic representation to be adapted [1.1]:

$$I_D = I_S \left(e^{n \frac{V_D}{V_T}} - 1 \right) \quad (1.1)$$

Here, $I_S \approx 10^{-12} \dots 10^{-6}$ A is the *reverse saturation current*, $n \approx 1 \dots 2$ is the *emission coefficient* and $V_T = kT/q \approx 26$ mV is the *temperature voltage* at room temperature.

Even though (1.1) actually applies only to $V_D \geq 0$ it is sometimes used for $V_D < 0$. For $V_D \ll -nV_T$ this results in a constant current $I_D = -I_S$ which is generally much smaller than the current that is actually flowing. Therefore, only the qualitative statement that a small negative current flows in the reverse region is correct. The shape of the current curve as shown in Fig. 1.3 can only be described with the help of additional equations (see Sect. 1.3).

$V_D \gg nV_T \approx 26 \dots 52$ mV applies to the forward region and the approximation

$$I_D = I_S e^{n \frac{V_D}{V_T}} \quad (1.2)$$

can be used. Then the voltage is:

$$V_D = nV_T \ln \frac{I_D}{I_S} = nV_T \ln 10 \cdot \log \frac{I_D}{I_S} \approx 60 \dots 120 \text{ mV} \cdot \log \frac{I_D}{I_S}$$

This means that the voltage increases by 60 ... 120 mV when the current rises by a factor of 10. With high currents the voltage drop $I_D R_B$ at the spreading resistance R_B must be taken into account, which occurs in addition to the voltage at the pn junction:

$$V_D = nV_T \ln \frac{I_D}{I_S} + I_D R_B$$

In this case it cannot be described in the form $I_D = I_D(V_D)$.

For simple calculations the diode can be regarded as a switch that is opened in the reverse region and is closed in the forward region. Given the assumption that the voltage is approximately constant in the forward region and that no current flows in the reverse region, the diode can be replaced by an ideal voltage-controlled switch and a voltage source with the forward voltage V_F (see Fig. 1.5a). Figure 1.5b shows the characteristic curve of this equivalent circuit which consists of two straight lines:

$$\begin{aligned} I_D &= 0 & \text{for } V_D < V_F &\rightarrow \text{switch open (a)} \\ V_D &= V_F & \text{for } I_D > 0 &\rightarrow \text{switch closed (b)} \end{aligned}$$

When the additional spreading resistance R_B is taken into consideration, we have:

$$I_D = \begin{cases} 0 & \text{for } V_D < V_F \rightarrow \text{switch open (a)} \\ \frac{V_D - V_F}{R_B} & \text{for } V_D \geq V_F \rightarrow \text{switch closed (b)} \end{cases}$$

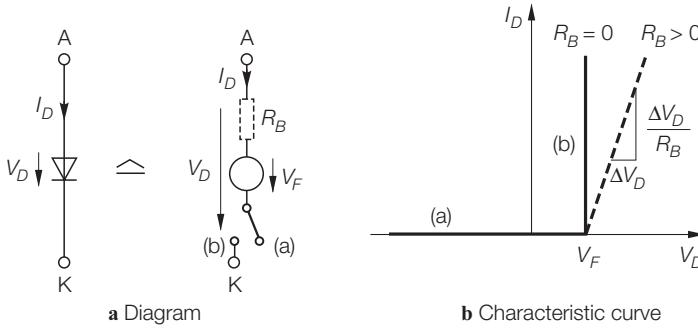


Fig. 1.5. Simple equivalent circuit diagram for a diode without (-) and with (- -) spreading resistance

The voltage V_F is $V_F \approx 0.6\text{ V}$ for silicon pn diodes and $V_F \approx 0.3\text{ V}$ for Schottky diodes. The corresponding circuit diagram and characteristic curve are shown in Fig. 1.5 as dashed lines. Different cases must be distinguished for both variations, that is, it is necessary to calculate with the switch open *and* closed and to determine the situation in which there is no contradiction. The advantage is that either case leads to linear equations which are easy to solve. In contrast, when using the e function according to (1.1), it is necessary to cope with an implicit nonlinear equation that can only be solved numerically.

Example: Figure 1.6 shows a diode in a bridge circuit. To calculate the voltages V_1 and V_2 and the diode voltage $V_D = V_1 - V_2$ it is assumed that the diode is in the reverse state, that is, $V_D < V_F = 0.6\text{ V}$ and the switch in the equivalent circuit is open. In this case, V_1 and V_2 can be determined by the voltage divider formula $V_1 = V_b R_2 / (R_1 + R_2) = 3.75\text{ V}$ and $V_2 = V_b R_4 / (R_3 + R_4) = 2.5\text{ V}$. This results in $V_D = 1.25\text{ V}$, which does not comply with the assumption. Consequently the diode is conductive and the switch in the equivalent circuit is closed; this leads to $V_D = V_F = 0.6\text{ V}$ and $I_D > 0$. From the nodal equations

$$\frac{V_1}{R_2} + I_D = \frac{V_b - V_1}{R_1} \quad , \quad \frac{V_2}{R_4} = I_D + \frac{V_b - V_2}{R_3}$$

it is possible to eliminate the unknown elements I_D and V_1 by adding the equations and inserting $V_1 = V_2 + V_F$; this leads to:

$$V_2 \left(\frac{1}{R_1} + \frac{1}{R_2} + \frac{1}{R_3} + \frac{1}{R_4} \right) = V_b \left(\frac{1}{R_1} + \frac{1}{R_3} \right) - V_F \left(\frac{1}{R_1} + \frac{1}{R_2} \right)$$

This results in $V_2 = 2.76\text{ V}$, $V_1 = V_2 + V_F = 3.36\text{ V}$ and in $I_D = 0.52\text{ mA}$ by substitution in one of the nodal equations. The initial condition $I_D > 0$ has been fulfilled, that is, there is no contradiction and the solution has been found.

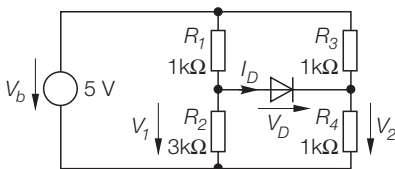


Fig. 1.6. Example for the demonstration of the use of the equivalent circuit of Fig. 1.5

1.1.3 Switching Performance

In many applications the diodes operate alternately in the forward mode and in the reverse mode, for example when rectifying alternating currents. The transition does not follow the static characteristic curve as the parasitic capacitance of the diode stores a charge that builds up in the forward state and is discharged in the reverse state. Figure 1.7 shows a circuit for determining the *switching performance* with an ohmic load ($L = 0$) or an ohmic-inductive load ($L > 0$). Applying a square wave produces the transitions shown in Fig. 1.8.

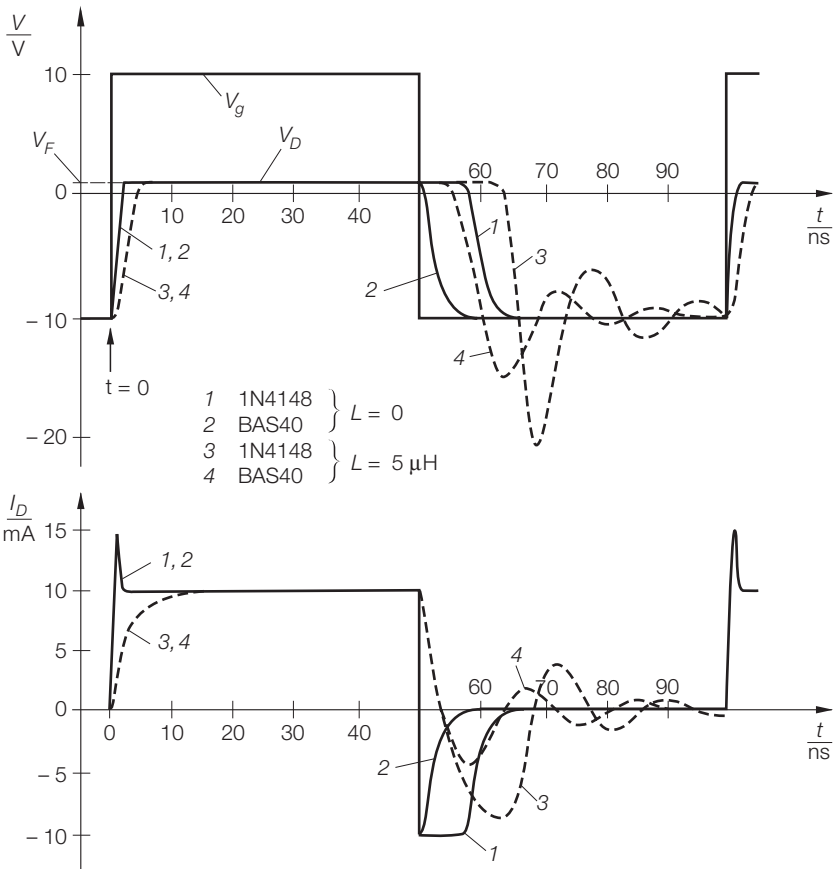
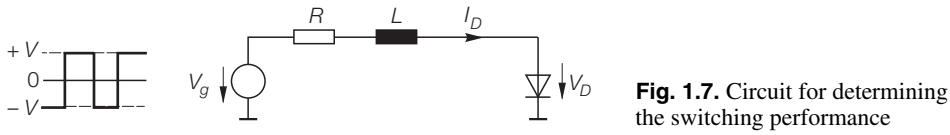


Fig. 1.8. Switching performance of the silicon diode 1N4148 and the Schottky diode BAS40 in the measuring circuit of Fig. 1.7 with $V = 10 \text{ V}$, $f = 10 \text{ MHz}$, $R = 1 \text{ k}\Omega$ and $L = 0$ or $L = 5 \mu\text{H}$

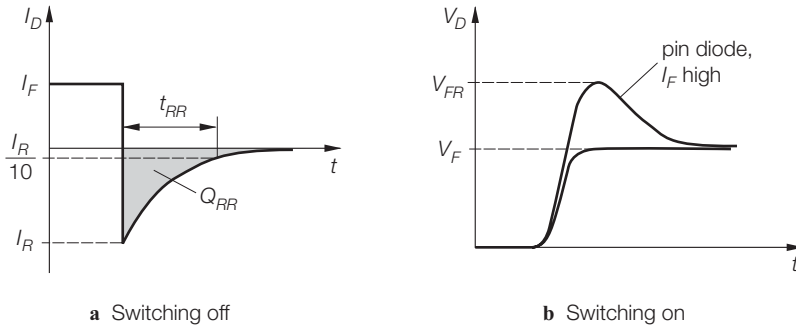


Fig. 1.9. Illustration of switching performance

Switching performance with ohmic load: With an ohmic load ($L = 0$) a current peak caused by the charge built up in the capacitance of the diode occurs when the circuit is activated. The voltage rises during this current peak from the previously existing reverse voltage to the forward voltage V_F which terminates the switch-on process. In pin diodes¹ higher currents may cause a voltage overshoot (see Fig. 1.9b) as these diodes initially have a higher spreading resistance R_B at the switch-on point. Subsequently the voltage declines to the static value in accordance with the decrease of R_B . When switching off there is a current in the opposite direction until the capacitance is discharged; then the current returns to zero and the voltage drops to the reverse voltage. Since the capacitance of Schottky diodes is much lower than that of silicon diodes of the same size, their turn-off time is significantly shorter (see Fig. 1.8). Therefore, Schottky diodes are preferred for rectifier diodes in switched power supplies with high cycle rates ($f > 20$ kHz), while the lower priced silicon diodes are used in rectifiers for the mains voltage ($f = 50$ Hz). When the frequency becomes so high that the capacitance discharge process is not completed before the next conducting state starts, the rectification no longer takes place.

Switching performance with ohmic-inductive load: With an ohmic-inductive load ($L > 0$) the transition to the conductive state takes longer since the increase in current is limited by the inductivity; no current peaks occur. While the voltage rises relatively fast to the forward voltage, the current increases with the time constant $T = L/R$ of the load. During switch-off the current first decreases with the time constant of the load until the diode cuts off. Then, the load and the capacitance of the diode form a series resonant circuit, and the current and the voltage perform damped oscillations. As shown in Fig. 1.8 high reverse voltages may arise which are much higher than the static reverse voltage and consequently require a high diode breakthrough voltage.

Figure 1.9 shows the typical data for *reverse recovery (RR)* and *forward recovery (FR)*. The *reverse recovery time* t_{RR} is the period measured from the moment at which the current passes through zero until the moment at which the reverse current drops to 10 %² of its maximum value I_R . Typical values range from $t_{RR} < 100$ ps for fast Schottky diodes to $t_{RR} = 1 \dots 20$ ns for small-signal silicon diodes or $t_{RR} > 1$ μ s for rectifier diodes. The *reverse recovery charge* Q_{RR} transported during the capacitance discharge corresponds to

¹ pin diodes have a nondoped (*intrinsic*) or slightly doped layer between the p and n layers in order to achieve a higher breakthrough voltage.

² With rectifier diodes the measurement is sometimes taken at 25 %.

the area below the x axis (see Fig. 1.9a). Both parameters depend on the previously flowing forward current I_F and the cutoff speed; therefore the data sheets show either information on the measuring conditions or the measuring circuit. An approximation is $Q_{RR} \sim I_F$ and $Q_{RR} \sim |I_R|t_{RR}$ [1.2]; this means that in a first approximation the reverse recovery time is proportional to the ratio of the forward and reverse current: $t_{RR} \sim I_F/|I_R|$. However, this approximation only applies to $|I_R| < 3 \dots 5 \cdot I_F$, in other words, t_{RR} can not be reduced endlessly. In pin diodes featuring a high breakdown voltage, the high cutoff speed may even cause the breakdown to occur far below the static breakdown voltage V_{BR} if the reverse voltage at the diode increases sharply before the weakly doped i-layer is free of charge carriers. With the transition to the forward state the *forward recovery voltage* V_{FR} occurs, which also depends on the actual switching conditions [1.3]; data sheets quote a maximum value for V_{FR} , typically $V_{FR} = 1 \dots 2.5$ V.

1.1.4 Small-Signal Response

The performance of the diode when controlled by *small* signals around an operating point characterized by $V_{D,A}$ and $I_{D,A}$ is called the *small-signal response*. In this case, the nonlinear characteristic given in (1.1) can be replaced by a tangent to the operating point; with the small-signal parameters

$$i_D = I_D - I_{D,A} \quad , \quad v_D = V_D - V_{D,A}$$

one arrives at:

$$i_D = \left. \frac{dI_D}{dV_D} \right|_A v_D = \frac{1}{r_D} v_D$$

From this the *differential resistance* r_D of the diode is derived:

$$r_D = \left. \frac{dV_D}{dI_D} \right|_A = \frac{nV_T}{I_{D,A} + I_S} \stackrel{I_{D,A} \gg I_S}{\approx} \frac{nV_T}{I_{D,A}} \quad (1.3)$$

Thus, the equivalent small-signal circuit for the diode consists of a resistance with the value r_D ; with large currents r_D becomes very small and an additional spreading resistance R_B must be introduced (see Fig. 1.10).

The equivalent circuit shown in Fig. 1.10 is only suitable for calculating the small-signal response at low frequencies (0...10 kHz); therefore, it is called the *DC small-signal equivalent circuit*. For higher frequencies it is necessary to use the AC small-signal equivalent circuit given in Sect. 1.3.3.



Fig. 1.10. Small-signal equivalent circuit of a diode